

# MXD8651

SP5T Switch for Receive Diversity



This document contains information that is confidential and proprietary to Maxscend Technologies Inc. (Maxscend) and may not be reproduced in any form without express written consent of Maxscend. No transfer or licensing of technology is implied by this document.



## **General Description**

The MXD8651 is a low loss, high isolation SP5T switch with performance optimized for receive diversity routing applications.

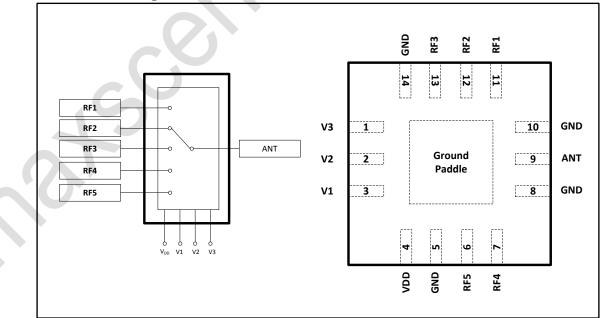
The MXD8651 is compatible with +1.0V control logic, which is a key requirement for most cellular transceivers. This part is packaged in a compact 2mm x 2mm x 0.55 mm, 14-pin, QFN package which allows for a small solution size with no need for external DC blocking capacitors (when no external DC is applied to the device ports).

#### Features

- Excellent insertion loss and isolation performance
  - 0.5 dB Typical Insertion Loss, Band 7
  - 25 dB typical Isolation, Band 7
- Multi-Band operation 700MHz to 2700MHz
- GPIO compatible to 1.8V Typ (1.0V min)
- Power handling +30dBm
- Compact 2mm x 2mm x 0.55 mm, in QFN package, MSL1
- No DC blocking capacitors required (unless external DC is applied to the RF ports)

## Applications

- Cellular Handset Applications
- Cellular modems and USB Devices
- Multi-mode GSM/Edge/WCDMA applications
- LTE applications



# **Functional Block Diagram and Pin Function**

#### Figure 1. Functional Block Diagram and Pinout (Top View)



# **Application Circuit**

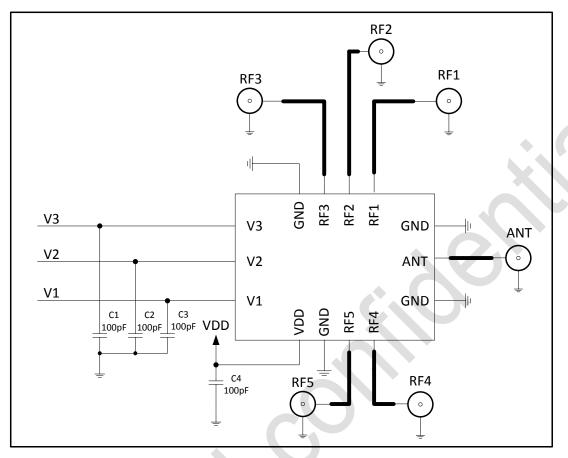


Figure 2. MXD8651 Evaluation Board Schematic

Pin No.	Nam	Description	Pin No.	Name	Description		
	е						
1	V3	Control Logic #3	8	GND	Ground		
2	V2	Control Logic #2	9	ANT	Antenna		
3	V1	Control Logic #1	10	GND	Ground		
4	$V_{DD}$	Power supply	11	RF1	RF port1		
5	GND	Ground	12	RF2	RF port2		
6	RF5	RF port5	13	RF3	RF port3		
7	RF4	RF port4	14	GND	Ground		
Ground Paddle	GND	Ground					

### **Table 1. Pin Description**

Note: Bottom ground paddles must be connected to ground.

# **Truth Table**

# Table 2.

C	ontrol	pins		Sv	ıts		
V1	V2	V3	RF1 RF2		RF3	RF4	RF5
1	0	0	Insertion Loss	Isolation	Isolation	Isolation	Isolation
0	1	0	Isolation	Insertion Loss	Isolation	Isolation	Isolation
1	1	0	Isolation	Isolation	Insertion Loss	Isolation	Isolation
0	0	1	Isolation	Isolation	Isolation	Insertion Loss	Isolation
1	0	1	Isolation	Isolation	Isolation	Isolation	Insertion Loss

Note: "1" = 1.0 V to 3.0 V. "0" = 0 V to 0.3 V. Insertion loss in the V1/2/3 = 110 state is 3dB lower than typical insertion loss with only one arm "on".



1

# **Recommended Operation Range**

#### Table 3. Recommended Operation Condition

Parameters	Symbol	Min	Тур	Max	Units
Operation Frequency	f1	0.1	-	3.0	GHz
Power supply	V <sub>DD</sub>	2.5	2.8	3.3	V
Switch Control Voltage High	V <sub>H</sub>	1.0	1.8	3.0	V
Switch Control Voltage Low	VL	0	0	0.3	V

# **Specifications**

## **Table 4. Electrical Specifications**

Demonster	0	Specification				Test Condition	
Parameter	Symbol	Min.	Typical	Max.	Units	(Note 2)	
DC Specifications					•		
Supply voltage	V <sub>DD</sub>	2.5	2.8	3.3	V		
Supply current	I <sub>DD</sub>		50	90	μA	Active mode	
Control voltage: High Low	V <sub>ctl_h</sub> V <sub>ctl_l</sub>	1.0 0		3.0 0.3	V V	$V_{DD}$ must be > $V_{CTL}$ at all times	
Control current	I <sub>CTL</sub>			5	μΑ		
Switching Speed, on RF to another			2	5	μs	10% to 90% RF	
Turn-on time	t <sub>on</sub>		5	10	μs	Time from V <sub>DD</sub> =0V to part ON and RF at 90%	
<b>RF Specifications</b>						·	
Insertion Loss							
Insertion Loss TRx - ANT	IL	2	0.40 0.40 0.50 0.50 0.55		dB dB dB dB dB	704MHz to 787MHz 815MHz to 960MHz 1710MHz to 1980MHz 2110MHz to 2170MHz 2300MHz to 2690MHz	
Isolation			0.55		ub		
Isolated TRx ports - ANT	ISO	45 45 35 30 25			dB dB dB dB dB	704MHz to 787MHz 815MHz to 960MHz 1710MHz to 1980MHz 2110MHz to 2170MHz 2300MHz to 2690MHz	
Harmonics (Pin =+16 dBr	n)						
Low Band, 2fo			-110		dBc	Pin = +16dBm, 50ohms, fo=824MHz	
Low Band, 3fo			-105		dBc	Pin = +16dBm, 50ohms, fo=824MHz	
High Band, 2fo	2fo		-105		dBc	Pin = +16dBm, 50ohms, fo=1980MHz	
High Band, 3fo	3fo		-100		dBc	Pin = +16dBm, 50ohms, fo=1980MHz	
High Band, 2fo			-100		dBc	Pin = +16dBm, 50ohms, fo=2570MHz	
High Band, 3fo			-100		dBc	Pin = +16dBm, 50ohms, fo=2570MHz	
VSWR			1.1	1.5		704-2690MHz	



# **Absolute Maximum Ratings**

## Table 5. Maximum ratings

Parameters	Symbol	Minimum	Maximum	Units	
Supply voltage	V <sub>DD</sub>	2.5	+3.3	V	
Control voltage (V1, V <sub>CTL</sub> V2, and V3)		0	+3.0	V	
RF input power (RF1 to RF5)	P <sub>IN</sub>		+30	dBm	
Operating temperature	T <sub>OP</sub>	-20	+85	°C	
Storage temperature	T <sub>STG</sub>	-40	+125	°C	
Electrostatic Discharge, Human Body Model (HBM), Class 1C	ESD		1000	v	

Note: Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device

// bbb C

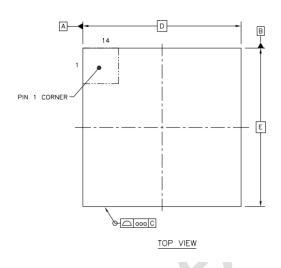
м

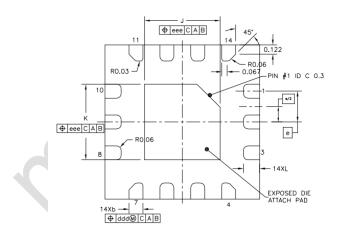
A3

Α2

-C SEATING PLANE

# **Package Outline Dimension**





DESCRIPTION		SYMBOL	MILLIMETER			
			MIN	NOM	MAX	
TOTAL THICKNESS		Α	0.50	0.55	0.60	
STAND OFF		A1	0		0.05	
MOLD THICKNESS		A2	0.35	0.40	0.45	
L/F THICKNESS	L/F THICKNESS			0.152 REF		
LEAD WIDTH	b	0.13	0.18	0.23		
BODY SIZE	х	D	1.95	2.00	2.05	
BUDT SIZE	Y	E	1.95	2.00	2.05	
LEAD PITCH	е	0.40 BSC				
EP SIZE	Х	J	0.93	0.98	1.03	
LP SIZE	Y	к	0.93	0.98	1.03	
LEAD LENGTH		L	0.16	0.21	0.26	
PACKAGE EDGE TOLEF	000	0.100				
MOLD FLATNESS	bbb	0.100				
COPLANARITY	ccc	0.080				
LEAD OFFSET	ddd	0.100				
EXPOSED PAD OFFSE	eee	0.100				

Figure 3. package outline dimension



## Marking Specification

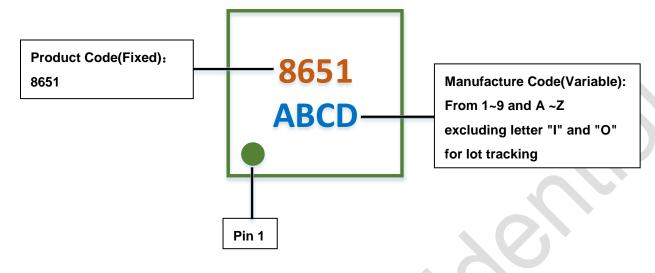
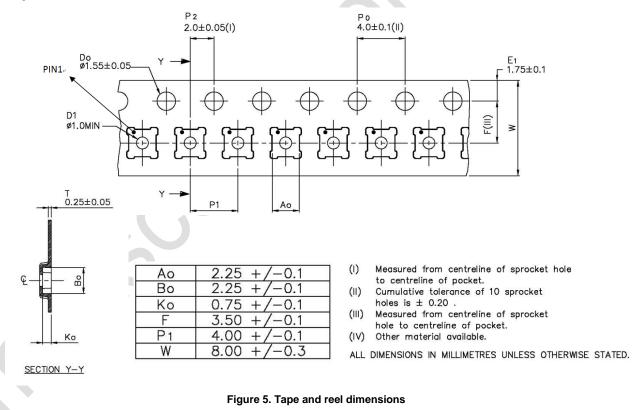


Figure 4. Marking specification (Top View)

## **Tape and Reel Dimensions**





**Reflow Chart** 

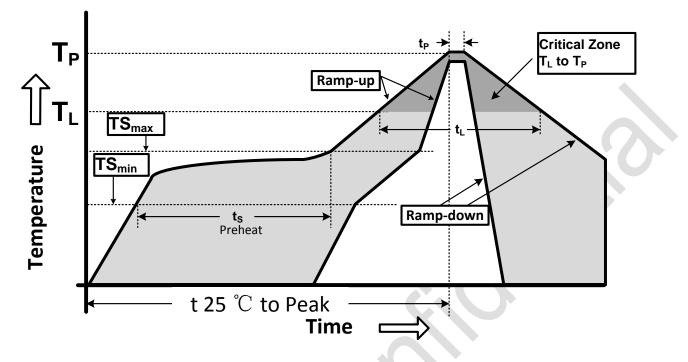


Figure 6. Recommended Lead-Free Reflow Profile

#### Table 6. Reflow condition

Profile Parameter	Lead-Free Assembly, Convection, IR/Convection			
Ramp-up rate $(TS_{max} to T_p)$	3℃/second max.			
Preheat temperature (TS <sub>min</sub> to TS <sub>max</sub> )	150℃ to 200℃			
Preheat time (t <sub>s</sub> )	60 - 180 seconds			
Time above TL , 217 $^{\circ}$ C (t <sub>L</sub> )	60 - 150 seconds			
Peak temperature (T <sub>p</sub> )	<b>260</b> ℃			
Time within 5°C of peak temperature( $t_p$ )	20 - 40 seconds			
Ramp-down rate	6℃/second max.			
Time 25°C to peak temperature	8 minutes max.			

# **ESD Sensitivity**

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

# **RoHS Compliant**

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.